





#### 60V N-CHANNEL ENHANCEMENT MODE VERTICAL DMOSFET IN SOT23

#### **Features**

- BV<sub>DSS</sub> > 60V
- $R_{DS(on)} \le 2.5\Omega$  @  $V_{GS} = 10V$
- Maximum continuous drain current I<sub>D</sub> = 200mA
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

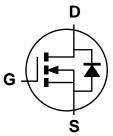
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.008 grams (approximate)



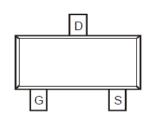
SOT23







Device symbol



Pin-Out Top View

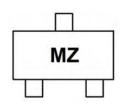
## **Ordering Information** (Note 4)

| Part Number | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |
|-------------|---------|--------------------|-----------------|-------------------|
| ZVN4106FTA  | MZ      | 7                  | 8               | 3000              |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

## **Marking Information**



MZ = Product Type Marking Code



**ZVN4106F** 

## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                | Symbol           | Value | Unit |
|-------------------------------|------------------|-------|------|
| Drain-Source Voltage          | $V_{DSS}$        | 60    | V    |
| Gate-Source Voltage           | V <sub>GSS</sub> | ±20   | V    |
| Continuous Drain Current      | I <sub>D</sub>   | 200   | mA   |
| Pulsed Drain Current (Note 5) | I <sub>DM</sub>  | 3     | А    |

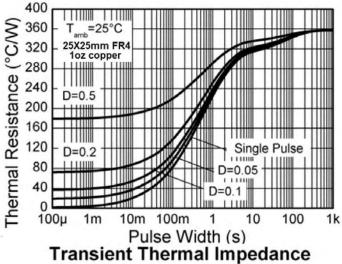
## **Thermal Characteristics**

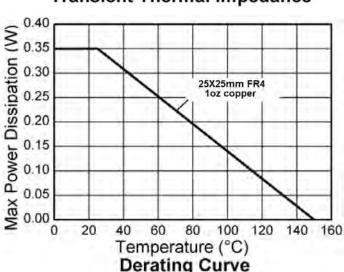
| Characteristic                          | Symbol            | Value          | Unit |      |
|---|-------------------|----------------|------|------|
| Power Dissipation                       | (Note 6)          | $P_{D}$        | 350  | mW   |
| Thermal Resistance, Junction to Ambient | (Note 6)          | $R_{	heta JA}$ | 357  | °C/W |
| Operating and Storage Temperature Range | $T_J$ , $T_{STG}$ | -55 to +150    | °C   |      |

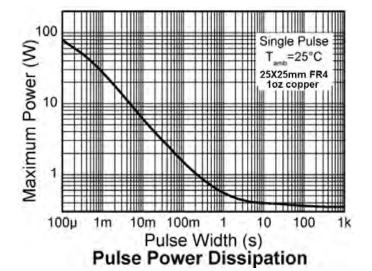
Notes: 5. De

- 5. Device mounted on minimum recommended pad layout test board, 10 s pulse duty cycle = 1%.
- 6. For a device mounted on 25mm X 25mm X 1.6mm FR-4 PCV with high coverage of single sided 1oz copper, in still air condition.

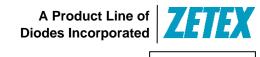
## **Thermal Characteristics**











**ZVN4106F** 

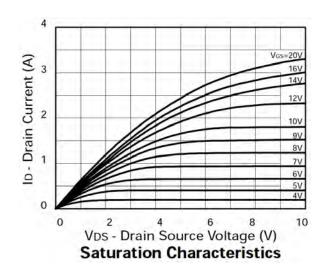
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

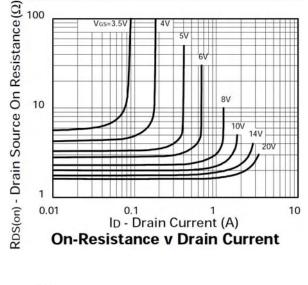
| Characteristic   | Symbol               | Min | Тур | Max      | Unit | Test Condition  |  |
|--|----------------------|-----|-----|----------|------|---|--|
| OFF CHARACTERISTICS (Note 7)                           |                      |     |     |          |      |   |  |
| Drain-Source Breakdown Voltage                         | BV <sub>DSS</sub>    | 60  | _   | _        | V    | $V_{GS} = 0V$ , $I_D = 10mA$  |  |
| Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C | I <sub>DSS</sub>     | l   | _   | 10<br>50 | μΑ   | $V_{DS} = 60V, V_{GS} = 0V$<br>$V_{DS} = 48V, V_{GS} = 0V, T_A = +125^{\circ}C$ |  |
| Gate-Source Leakage                                    | I <sub>GSS</sub>     | _   | _   | 100      | nA   | $V_{GS} = \pm 20V$ , $V_{DS} = 0V$  |  |
| On-State Drain Current                                 | I <sub>D(on)</sub>   | 1   | _   | -        | Α    | V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V                                    |  |
| ON CHARACTERISTICS (Note 7)                            |                      |     | ā.  |          |      |   |  |
| Gate Threshold Voltage                                 | V <sub>GS(th)</sub>  | 1.3 | _   | 3        | V    | $V_{DS} = V_{GS}$ , $I_D = 1mA$   |  |
| Static Drain-Source On-Resistance                      | R <sub>DS (on)</sub> |     | _   | 2.5<br>5 | Ω    | $V_{GS} = 10V, I_D = 500mA$<br>$V_{GS} = 5V, I_D = 200mA$                       |  |
| Forward Transconductance                               |                      | 150 | _   | -        | mS   | V <sub>DS</sub> = 25V, I <sub>D</sub> = 250mA                                   |  |
| DYNAMIC CHARACTERISTICS (Note 7)                       |                      |     |     |          |      |   |  |
| Input Capacitance                                      | C <sub>iss</sub>     | _   | _   | 35       | pF   | V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V,<br>f = 1.0MHz                      |  |
| Output Capacitance                                     | Coss                 | _   | _   | 25       | pF   |   |  |
| Reverse Transfer Capacitance                           | C <sub>rss</sub>     | _   | _   | 8        | pF   |   |  |
| Turn-On Delay Time                                     | t <sub>D(on)</sub>   | _   | _   | 5        | ns   | V <sub>DS</sub> = 25V, I <sub>D</sub> = 150mA                                   |  |
| Turn-On Rise Time                                      | t <sub>r</sub>       | _   | _   | 7        | ns   |   |  |
| Turn-Off Delay Time                                    | t <sub>D(off)</sub>  |     | _   | 6        | ns   |   |  |
| Turn-Off Fall Time                                     | t <sub>f</sub>       | _   | _   | 8        | ns   |   |  |

Notes: 7. Short duration pulse test used to minimize self-heating effect.

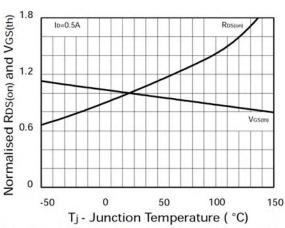


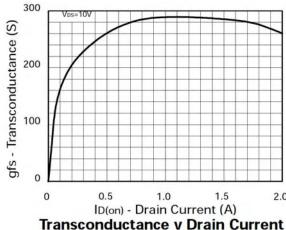
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)



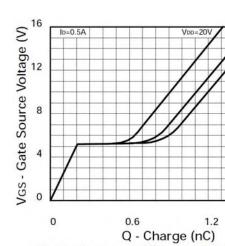


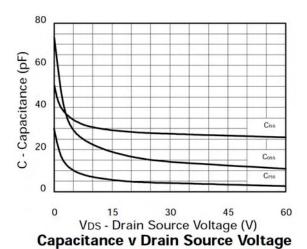
100





Normalised RDS(on) & VGS(th) v Temperature



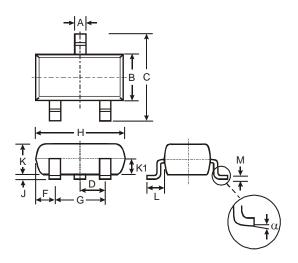


Gate Source Voltage v Gate Charge

1.8

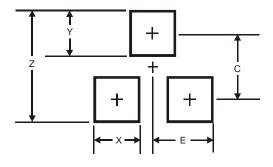


# **Package Outline Dimensions**



| SOT23                |       |      |       |  |
|----------------------|-------|------|-------|--|
| Dim                  | Min   | Max  | Тур   |  |
| Α                    | 0.37  | 0.51 | 0.40  |  |
| В                    | 1.20  | 1.40 | 1.30  |  |
| С                    | 2.30  | 2.50 | 2.40  |  |
| D                    | 0.89  | 1.03 | 0.915 |  |
| F                    | 0.45  | 0.60 | 0.535 |  |
| G                    | 1.78  | 2.05 | 1.83  |  |
| Н                    | 2.80  | 3.00 | 2.90  |  |
| J                    | 0.013 | 0.10 | 0.05  |  |
| K                    | 0.903 | 1.10 | 1.00  |  |
| K1                   | -     | -    | 0.400 |  |
| L                    | 0.45  | 0.61 | 0.55  |  |
| M                    | 0.085 | 0.18 | 0.11  |  |
| α                    | 0°    | 8°   | -     |  |
| All Dimensions in mm |       |      |       |  |

# **Suggested Pad Layout**



| Dimensions | Value (in mm) |
|------------|---------------|
| Z          | 2.9           |
| Х          | 0.8           |
| Υ          | 0.9           |
| С          | 2.0           |
| E          | 1.35          |





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